CLAIMS

[Claim 1]

A magnetoresistance effect element comprising:

a barrier layer;

a reference layer formed on one surface of the barrier layer;

a free layer formed on another surface of the barrier layer; and

a pin layer placed on an opposite side of the reference layer from the barrier layer, wherein

the pin layer includes Pt, Co, Ru, Co, and Pt layers stacked in this order, and a layer including Ni, and includes a structure obtained by stacking Ni, Co, Pt, Co, Ru, Co, Pt, Co, and Ni layers in this order.